

STRAINED SILICON MOSFETS HAVING.....
Inventors: Qi XIANG
Attorney: Ronald Coslick - 039153-0685
FOLEY & LARDNER LLP - (310) 975-7964

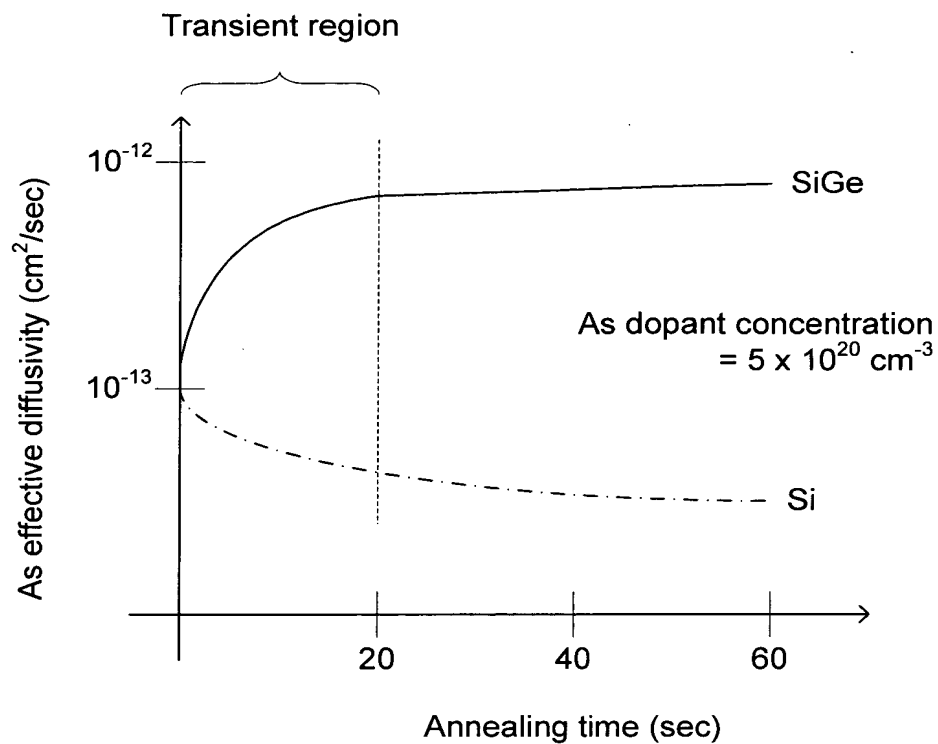
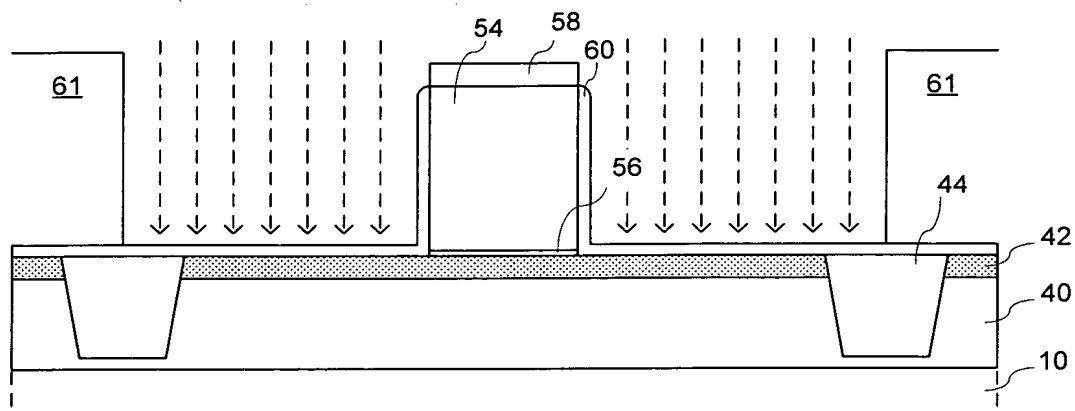


Figure 4
Prior Art



This cross-sectional view shows a semiconductor device with a central raised structure. The device includes a substrate (10) with a central region (40) and side regions (42). A central raised structure (54) is formed on the central region (40). The raised structure has a top surface (58) and a side surface (60). A layer (56) is formed on the side surface (60) of the raised structure. A layer (44) is formed on the side regions (42). A dashed line (62) indicates a boundary or interface within the device.

62 62

Figure 5f